Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Low reverse recovery current and low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- · Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------------|---------------------------------|---|--|-----|-----|------|------|
| V_{RRM} | repetitive peak reverse voltage | | | - | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2 | | - | - | 8 | Α |
| Static characte | eristics | | | | | | |
| V_{F} | forward voltage | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | | _ | 1.4 | 1.85 | V |
| Dynamic characteristics | | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$ | | - | 19 | - | ns |

Hyperfast power diode

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|------------------------|--------------------|----------------|
| 1 | K | cathode | mb | K — A |
| 2 | Α | anode | | 001aaa020 |
| mb | mb | mounting base; cathode | | |
| | | | TO-220AC (SOD59) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| BYC8-600 | TO-220AC | plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC | SOD59 | | |

Hyperfast power diode

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|---------------------------------|--|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V_{RWM} | crest working reverse voltage | | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2 | - | 8 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le 109$ °C; square-wave pulse | - | 16 | Α |
| I _{FSM} | non-repetitive peak | t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse | - | 80 | Α |
| | forward current | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse | - | 88 | Α |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| Tj | junction temperature | | - | 150 | °C |

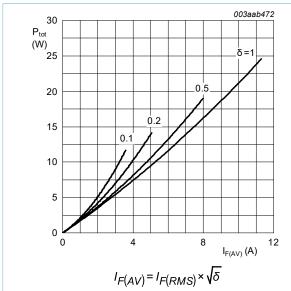


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

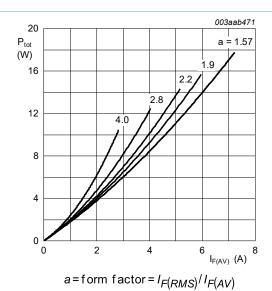


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|---------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 3</u> | - | - | 2.2 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | | - | 60 | - | K/W |

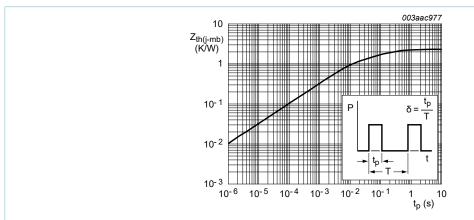


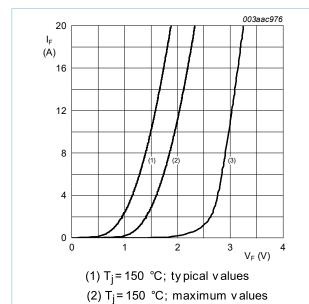
Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

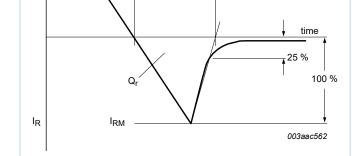
Hyperfast power diode

9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|---|-----|-----|------|------|
| Static chara | acteristics | | | | | |
| V _F | forward voltage | I _F = 8 A; T _j = 25 °C | - | 2 | 2.9 | V |
| | | I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u> | - | 1.4 | 1.85 | V |
| | | I _F = 16 A; T _j = 150 °C | - | 1.7 | 2.3 | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | - | 9 | 150 | μA |
| | | V _R = 600 V; T _j = 100 °C | - | 1.1 | 3 | mA |
| Dynamic ch | naracteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 5}}{}$ | - | 30 | 52 | ns |
| | | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$ | - | 19 | - | ns |
| | | $I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 5$ | - | 32 | 40 | ns |
| I _{RM} | peak reverse recovery current | I_F = 8 A; V_R = 400 V; dI_F/dt = 50 A/ μ s; T_j = 125 °C | - | 1.5 | 5.5 | А |
| | | $I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 100 \text{ °C}$ | - | 9.5 | 12 | А |
| Q _r | recovered charge | $I_F = 1 \text{ A}$; $V_R = 100 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$ | - | 12 | - | nC |
| V_{FR} | forward recovery voltage | $I_F = 10 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6 | - | 8 | 10 | V |





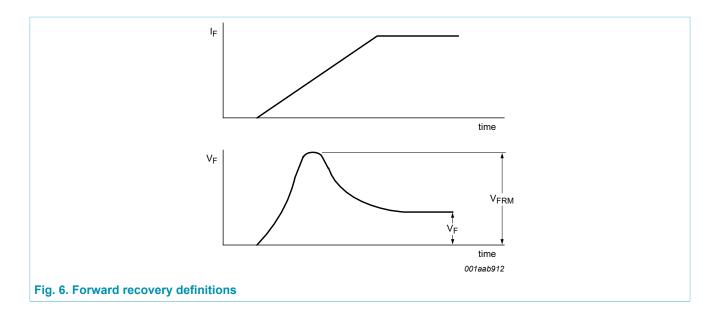
 dI_F

dt

Fig. 5. Reverse recovery definitions; ramp recovery

(3) T_j =25 °C; maximum values Fig. 4. Forward current as a function of forward voltage

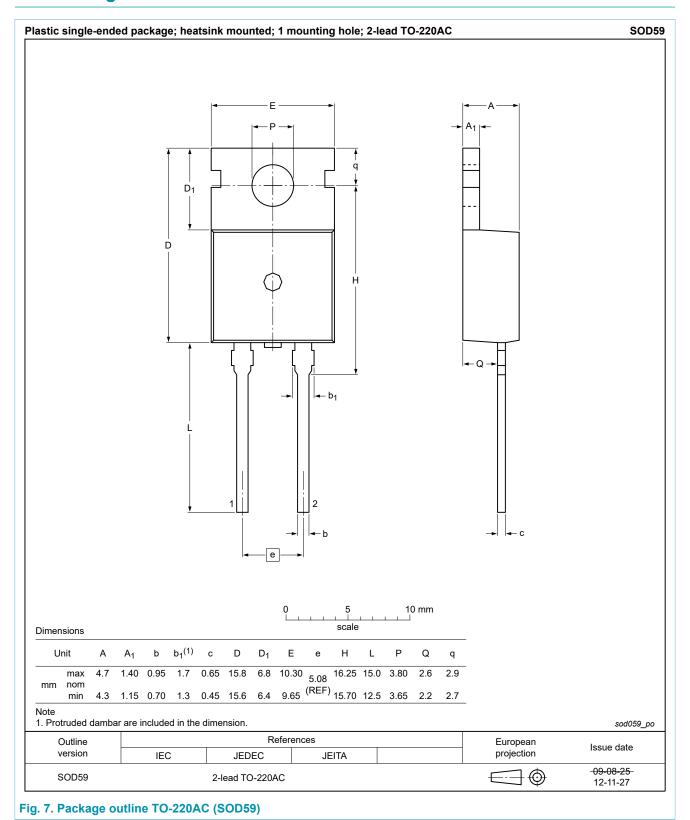
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10. Package outline



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11. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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